

# ISA1602AM1

FOR LOW FREQUENCY AMPLIFY APPLICATION  
SILICON PNP EPITAXIAL TYPE

## DESCRIPTION

ISA1602AM1 is a mini package resin sealed silicon PNP epitaxial transistor, It is designed for low frequency voltage application.

## FEATURE

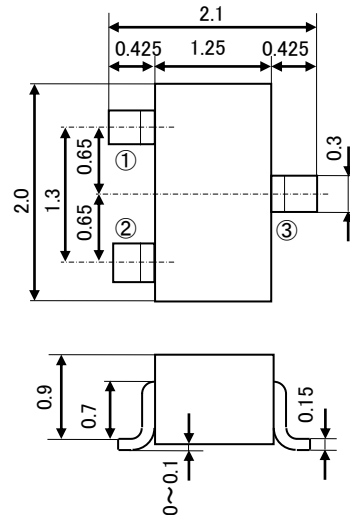
- Small collector to emitter saturation voltage.  
 $V_{CE(sat)} = -0.3V \text{ max } (@I_C = -100mA / I_B = -10mA)$
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting

## APPLICATION

For small type machine low frequency voltage amplify application

## OUTLINE DRAWING

Unit : mm



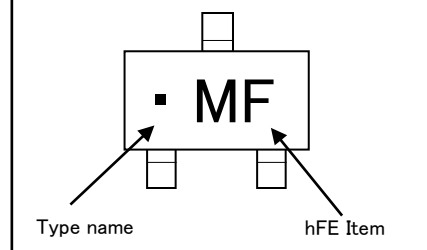
## TERMINAL CONNECTER

- ① : BASE JEITA : SC-70  
② : EMITTER JEDEC : -  
③ : COLLECTOR

## MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to Base voltage	$V_{CBO}$	-60	V
Emitter to Base voltage	$V_{EBO}$	-6	V
Collector to Emitter voltage	$V_{CEO}$	-50	V
Collector current	$I_C$	-200	mA
Collector dissipation	$P_C$	200	mW
Junction temperature	$T_J$	+150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

## MARKING



## ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Test conditions	Limits			Unit
			Min	Typ	Max	
C to E breakdown voltage	$V_{(BR)CEO}$	$I_C = -100 \mu\text{A}, R_{BE} = \infty$	-50	-	-	V
Collector cut off current	$I_{CBO}$	$V_{CB} = -60V, I_E = 0mA$	-	-	-0.1	$\mu\text{A}$
Emitter cut off current	$I_{EBO}$	$V_{EB} = -6V, I_C = 0mA$	-	-	-0.1	$\mu\text{A}$
DC forward current gain ※	$h_{FE}$	$V_{CE} = -6V, I_C = -1mA$	150	-	500	-
DC forward current gain	$h_{FE}$	$V_{CE} = -6V, I_C = -0.1mA$	90	-	-	-
C to E Saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$	-	-	-0.3	V
Gain bandwidth product	$f_T$	$V_{CE} = -6V, I_E = 10mA$	-	200	-	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6V, I_E = 0, f = 1MHz$	-	4.0	-	pF
Noise figure	NF	$V_{CE} = -6V, I_E = 0.3mA, f = 100Hz, R_G = 10k \Omega$	-	-	20	dB

※) It shows hFE classification at right table.

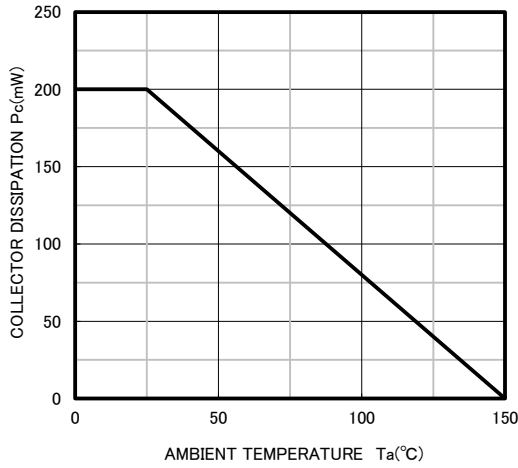
Item	E	F
hFE	150 ~ 300	250 ~ 500

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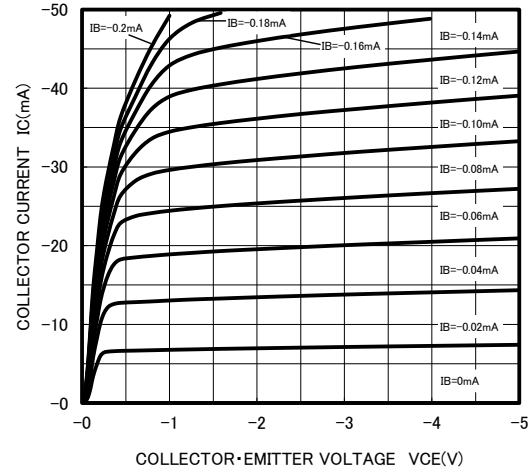
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## TYPICAL CHARACTERISTICS

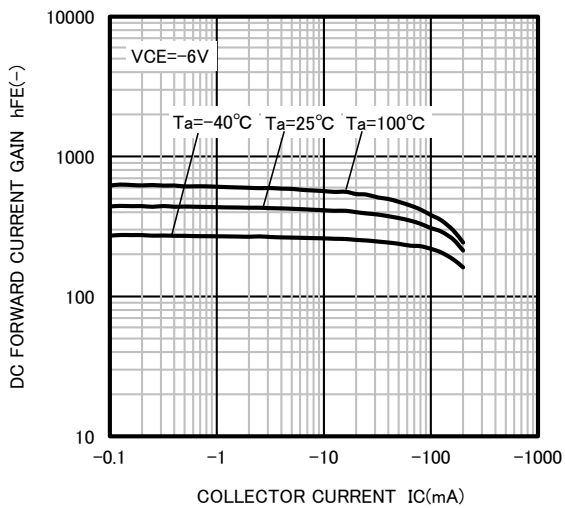
COLLECTOR DISSIPATION  
VS AMBIENT TEMPERATURE



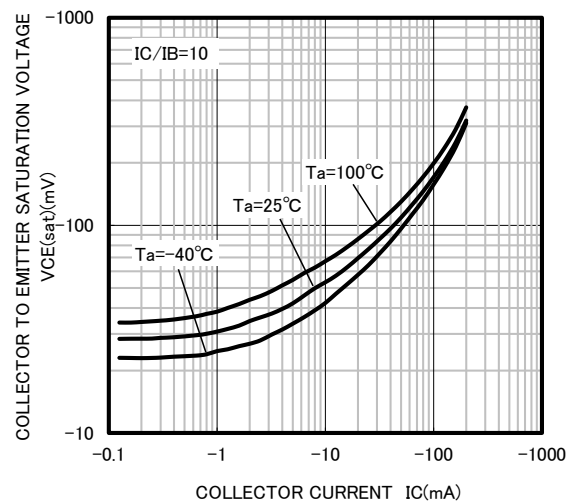
COMMON EMITTER OUTPUT



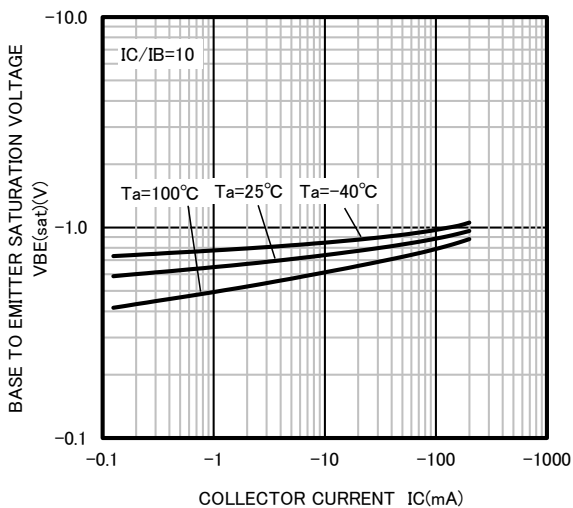
DC FORWARD CURRENT GAIN  
VS COLLECTOR CURRENT



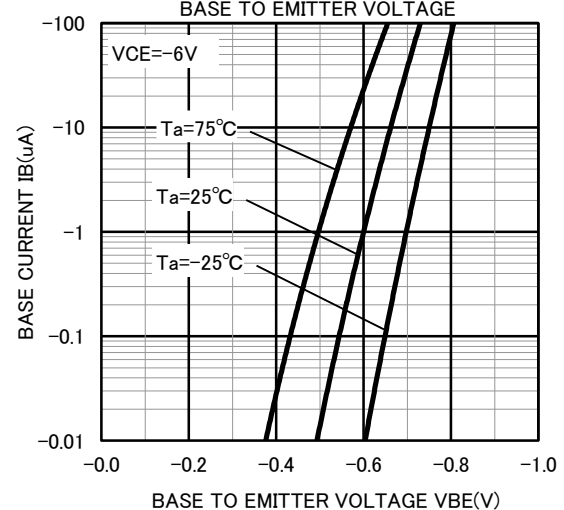
COLLECTOR TO EMITTER SATURATION VOLTAGE  
VS COLLECTOR CURRENT



BASE TO EMITTER SATURATION VOLTAGE  
VS COLLECTOR CURRENT



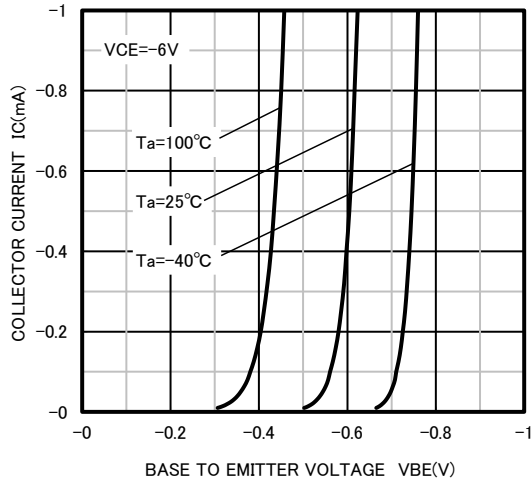
BASE CURRENT VS.  
BASE TO EMITTER VOLTAGE



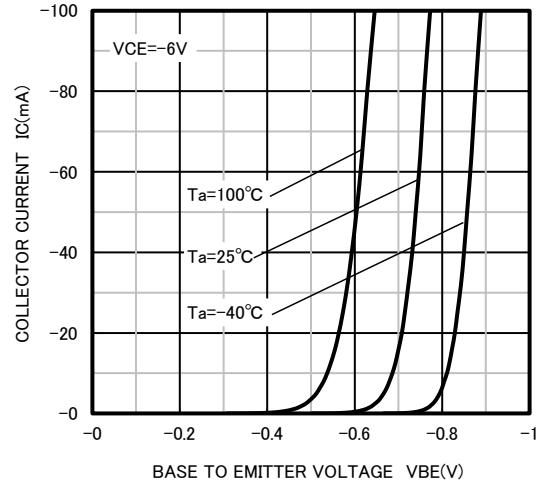
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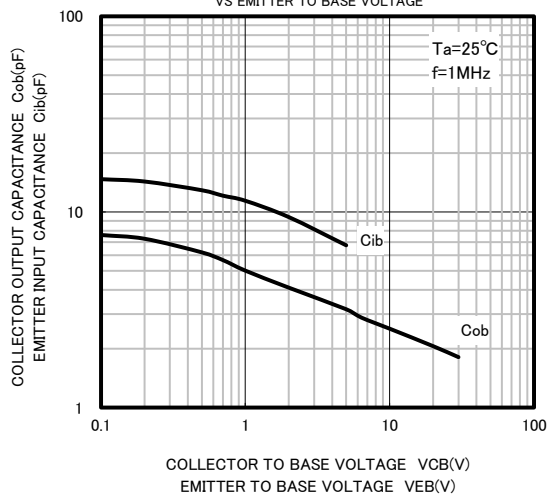
COMMON EMITTER TRANSFER



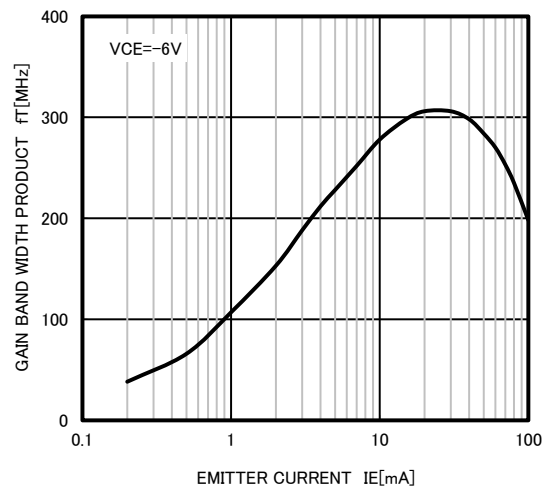
COMMON EMITTER TRANSFER



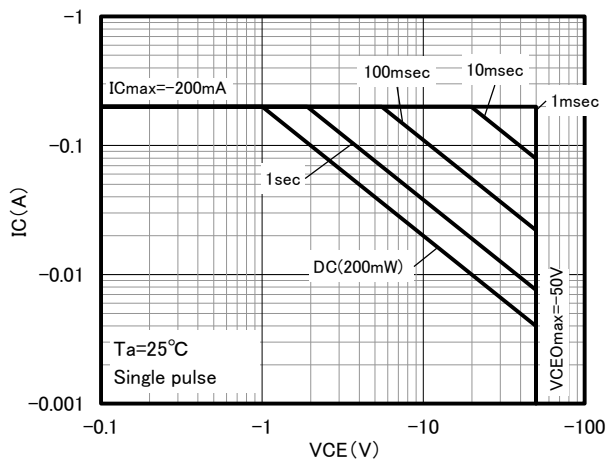
COLLECTOR OUTPUT CAPACITANCE  
VS COLLECTOR TO BASE VOLTAGE  
EMITTER INPUT CAPACITANCE  
VS EMITTER TO BASE VOLTAGE



GAIN BAND WIDTH PRODUCT  
VS. EMITTER CURRENT



ASO



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